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(1)

1/1 - (C) FILE CA
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ED - Entered STN: 12 Jul 1991
TI - Excimer laser patterning associated with silylation and oxygne reactiv ion etching
IN - Fukui, Akiyoshi; Tokui, Akira
PA - Mitsubishi Electric Corp., Japan
SO - Jpn. Kokai Tokkyo Koho, 4 pp.
CODEN: JKXXAF
DT - Patent
LA - Japanese
IC - ICM G03F007/038
ICS G03F007/36;G03F7/38;H01L21/027
ICA - H01L021-22; H01L021-266
CC - 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 76
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PN	JP3006566	A	19910114	JP 1989-141765	19890602
PR	JP 1989-141765		19890602		

AB - In patterning of resist for manuf. of semiconductor device, a novolak formed on a substrate is selectively irradiated by excimer laser beam silylated and dry-developed by O plasma reactive ion etching. Thus, a semiconductor substrate was spin-coated with a novolak film, selective irradiated by KrF excimer laser, treated by hexamethyldisilazane in va at high temp., and dry-etched by O plasma to give a precise pattern ha rectangular section.
ST - patterning resist excimer laser silylation; novolak methylsilylamine silylation dry etching; oxygen plasma novolak resist etching; semiconductor device patterning excimer laser
IT - Semiconductor devices
(patterning of resist for, excimer laser irradn. and silylation and oxygen plasma reactive ion etching in)
IT - Phenolic resins, uses and miscellaneous
RL: USES (Uses)
(novolak, excimer laser resists from, patterning of, silylation and oxygen plasma reactive ion etching in, for semiconductor device)
IT - Resists
(photo-, patterning of, excimer laser irradn. and silylation and oxy plasma reactive ion etching in)
IT - 999-97-3, Hexamethyldisilazne 34478-34-7, Trimethylsilyldiamine
RL: USES (Uses)
(photoresist modified by, for patterning of semiconductor device by excimer laser irradn. and oxygen plasma reactive ion etching)